

Europäisches Patentamt
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(11) EP 0 918 384 A3

(12) EUROPEAN PATENT APPLICATION

(88) Date of publication A3:
01.03.2000 Bulletin 2000/09

(51) Int. Cl.⁷: H01S 3/19

(43) Date of publication A2:
26.05.1999 Bulletin 1999/21

(21) Application number: 99102778.0

(22) Date of filing: 18.01.1996

(84) Designated Contracting States:
DE FR GB NL

(30) Priority: 20.01.1995 JP 741495
13.06.1995 JP 14598695

(62) Document number(s) of the earlier application(s) in
accordance with Art. 76 EPC:
96100699.6 / 0 723 322

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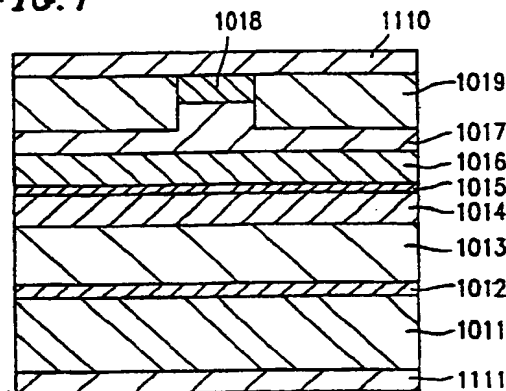
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(54) Semiconductor light emitting device and method for fabricating the same

(57) In a II-VI group semiconductor laser, on an n type GaAs substrate, n type ZnSe layer, a multiquantum well layer of a ZnCdSe well layer and a ZnSe barrier layer, and a p type ZnSe layer are deposited in this order. A polycrystalline ZnO layer is provided on both sides of the p type ZnSe layer for constricting current. Multifilm reflecting mirrors, respectively constituted with a polycrystalline SiO₂ layer and a polycrystalline TiO₂ layer, for obtaining laser oscillation are provided on the p type ZnSe layer as well as on a surface of the n type ZnSe layer exposed by etching the GaAs substrate. Furthermore, a p type AuPd electrode and an n type AuGeNi electrode are respectively provided. Alternatively, on an n type GaAs substrate, an n type ZnSe epitaxial layer, an n type ZnMgSSe cladding layer, an n type ZnSSe optical waveguide layer, a ZnCdSe active layer, a p type ZnSSe optical waveguide layer, a p type ZnMgSSe cladding layer, a p type ZnTe contact layer and a polycrystalline ZnO burying layer are respectively formed. Furthermore, a p type AuPd electrode and an n type In electrode are respectively provided.

FIG. 1



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EUROPEAN SEARCH REPORT

Application Number
EP 99 10 2778

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Category	Citation of document with indication, where appropriate, of relevant passages	Relevant to claim	CLASSIFICATION OF THE APPLICATION (Int.Cl.7)
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A	* column 4, line 13-26 * * column 13, line 17 - column 14, line 3 * * figure 10 *	2	
A	--- HAYASHI S ET AL: "ZNSE-BASED LASER DIODES ON P-GAAS WITH CURRENT CONFINEMENT BY NITROGEN ION BOMBARDMENT" INTERNATIONAL CONFERENCE ON SOLID STATE DEVICES AND MATERIALS, JA, JAPAN SOCIETY OF APPLIED PHYSICS, TOKYO, page 59-61 XP000409372 * the whole document *	1-6	
A	--- PATENT ABSTRACTS OF JAPAN vol. 018, no. 225 (E-1541), 22 April 1994 (1994-04-22) & JP 06 021567 A (SHIMADZU CORP), 28 January 1994 (1994-01-28) * abstract *	1-6	
A	--- PATENT ABSTRACTS OF JAPAN vol. 017, no. 115 (E-1330), 10 March 1993 (1993-03-10) & JP 04 297077 A (NIPPON TELEGR & TELEPH CORP), 21 October 1992 (1992-10-21) * abstract *	1	<div>TECHNICAL FIELDS SEARCHED (Int.Cl.7)</div> <div>H01S</div>
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Place of search THE HAGUE		Date of completion of the search 7 January 2000	Examiner Claessen, L
<div>CATEGORY OF CITED DOCUMENTS</div> <div> X : particularly relevant if taken alone Y : particularly relevant if combined with another document of the same category A : technological background O : non-written disclosure P : intermediate document T : theory or principle underlying the invention E : earlier patent document, but published on, or after the filing date D : document cited in the application L : document cited for other reasons & : member of the same patent family, corresponding document </div>			

EPO FORM 1503 03.82 (P04C01)

ANNEX TO THE EUROPEAN SEARCH REPORT
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